

**Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	I <sub>D</sub> T <sub>C</sub> = +25°C
30V	2.0mΩ @ V <sub>GS</sub> = 10V	100A
	3.0mΩ @ V <sub>GS</sub> = 4.5V	100A

**Description and Applications**

This new generation MOSFET is designed to minimize R<sub>DS(ON)</sub>, yet maintain superior switching performance. This device is ideal for use in power management and load switch.

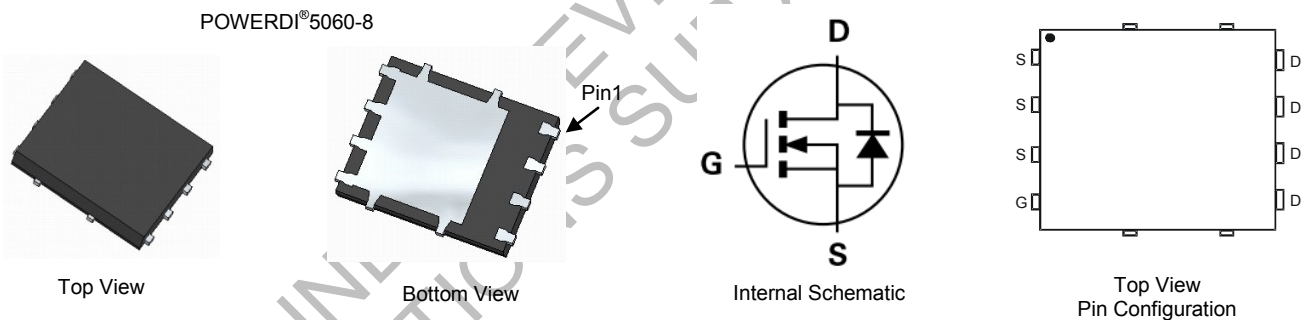
- DC-DC Converters
- Load Switch

**Features**

- Thermally Efficient Package-Cooler Running Applications
- <1.1mm Package Profile – Ideal for Thin Applications
- High Conversion Efficiency
- Low R<sub>DS(ON)</sub> – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. “Green” Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**

**Mechanical Data**

- Case: POWERDI®5060-8
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.097 grams (Approximate)

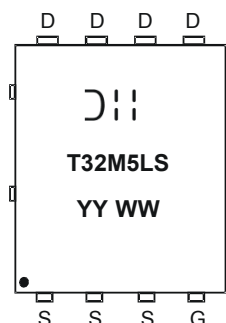


**Ordering Information (Note 4)**

Part Number	Case	Packaging
DMT32M5LPS-13	POWERDI®5060-8	2,500 / Tape & Reel

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
  2. See [http://www.diodes.com/quality/lead\\_free.html](http://www.diodes.com/quality/lead_free.html) for more information about Diodes Incorporated’s definitions of Halogen- and Antimony-free, “Green” and Lead-free.
  3. Halogen- and Antimony-free “Green” products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

**Marking Information**



= Manufacturer’s Marking  
 T32M5LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY = Year (ex: 16 = 2016)  
 WW = Week (01 to 53)

**Maximum Ratings** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current, V <sub>GS</sub> = 10V (Note 6)	Steady State	T <sub>C</sub> = +25°C	I <sub>D</sub>	100	A
		T <sub>C</sub> = +100°C	I <sub>D</sub>	100	A
Maximum Continuous Body Diode Forward Current (Note 6)			I <sub>S</sub>	80	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	120	A
Avalanche Current, L=0.1mH			I <sub>AS</sub>	50	A
Avalanche Energy, L=0.1mH			E <sub>AS</sub>	140	mJ

**Thermal Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	T <sub>A</sub> = 25°C	P <sub>D</sub>	3.2	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θJA</sub>	46	°C/W
Total Power Dissipation (Note 6)	T <sub>C</sub> = 25°C	P <sub>D</sub>	100	W
Thermal Resistance, Junction to Case (Note 6)		R <sub>θJC</sub>	1.5	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

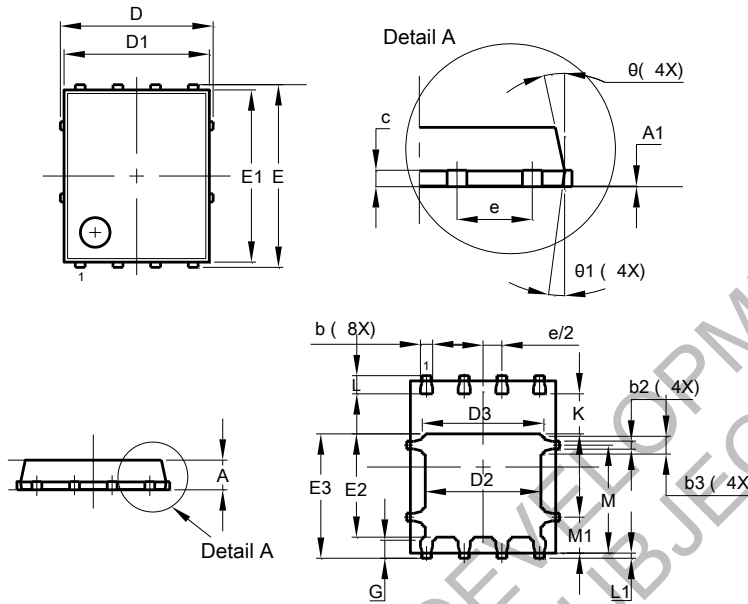
**Electrical Characteristics** (@T<sub>C</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	-	-	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	-	-	1	µA	V <sub>DS</sub> = 24V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±100	nA	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1	-	3	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 1mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	-	1.6	2.0	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A
		-	2.3	3.0		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 30A
Diode Forward Voltage	V <sub>SD</sub>	-	0.8	1.1	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 30A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>ISS</sub>	-	4950	-	pF	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	C <sub>OSS</sub>	-	2000	-		
Reverse Transfer Capacitance	C <sub>RSS</sub>	-	205	-		
Gate Resistance	R <sub>g</sub>	-	0.6	-	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Q <sub>g</sub>	-	38.0	-	nC	V <sub>DS</sub> = 15V, I <sub>D</sub> = 20A
Total Gate Charge (V <sub>GS</sub> = 10V)	Q <sub>g</sub>	-	86.3	-		
Gate-Source Charge	Q <sub>gs</sub>	-	14.0	-		
Gate-Drain Charge	Q <sub>gd</sub>	-	13.5	-		
Turn-On Delay Time	t <sub>D(ON)</sub>	-	9.3	-	ns	V <sub>DD</sub> = 15V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A, R <sub>G</sub> = 1.6Ω
Turn-On Rise Time	t <sub>r</sub>	-	15.3	-		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	-	35.9	-		
Turn-Off Fall Time	t <sub>f</sub>	-	12.0	-		
Body Diode Reverse Recovery Time	t <sub>RR</sub>	-	30.4	-	ns	I <sub>S</sub> = 15A, di/dt = 500A/µs
Body Diode Reverse Recovery Charge	Q <sub>RR</sub>	-	52.3	-	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
  - Thermal resistance from junction to soldering point (on the exposed drain pad).
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to production testing.

**Package Outline Dimensions**

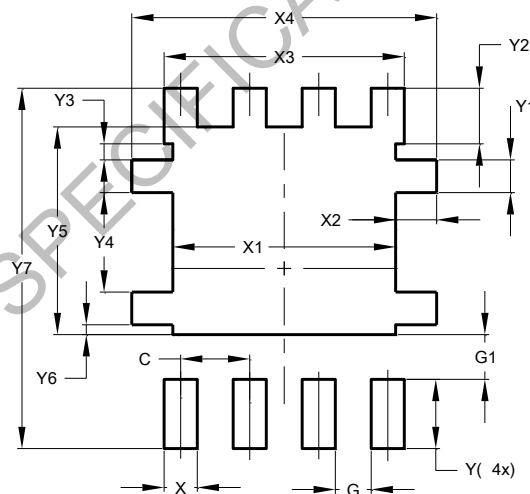
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



POWERDI <sup>®</sup> 5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	—
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	—	—
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

**Suggested Pad Layout**

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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